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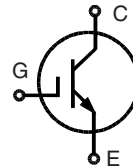
[IXER60N120](#)

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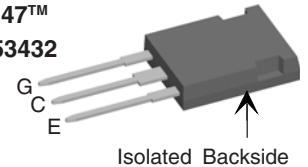
sales@integrated-circuit.com

NPT³ IGBT
in ISOPLUS 247™

I_{C25} = 95 A
V_{CES} = 1200 V
V_{CE(sat) typ.} = 2.1 V



ISOPLUS 247™
E153432



G = Gate C = Collector E = Emitter

IGBT		
Symbol	Conditions	Maximum Ratings
V _{CES}	T _{VJ} = 25°C to 150°C	1200 V
V _{GES}		± 20 V
I _{C25}	T _C = 25°C	95 A
I _{C90}	T _C = 90°C	60 A
I _{CM} V _{CEK}	V _{GE} = ±15 V; R _G = 22 Ω; T _{VJ} = 125°C RBSOA, Clamped inductive load; L = 100 μH	100 V _{CES} A
t _{SC} (SCSOA)	V _{CE} = 900 V; V _{GE} = ±15 V; R _G = 22 Ω; T _{VJ} = 125°C non-repetitive	10 μs
P _{tot}	T _C = 25°C	375 W

Features

- NPT³ IGBT
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- ISOPLUS 247™ package
 - isolated back surface
 - low coupling capacity between pins and heatsink
 - high reliability
 - industry standard outline

Symbol	Conditions	Characteristic Values (T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _{CE(sat)}	I _C = 60 A; V _{GE} = 15 V; T _{VJ} = 25°C T _{VJ} = 125°C	2.1	2.7	V	
V _{GE(th)}	I _C = 2 mA; V _{GE} = V _{CE}	4.5		V	
I _{CES}	V _{CE} = V _{CES} ; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C	0.1		0.1 mA	
I _{GES}	V _{CE} = 0 V; V _{GE} = ± 20 V			200 nA	
t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Inductive load, T _{VJ} = 125°C V _{CE} = 600 V; I _C = 60 A V _{GE} = ±15 V; R _G = 22 Ω		80	ns	
				50	ns
				680	ns
				30	ns
				7.2	mJ
				4.8	mJ
C _{ies}	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		3.8	nF	
Q _{Gon}	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 50 A		350	nC	
R _{thJC} R _{thJH}		0.66		0.33 KW KW	

Applications

- single switches and with complementary free wheeling diodes
- choppers
- phaselegs, H bridges, three phase bridges e.g. for
 - power supplies, UPS
 - AC, DC and SR drives
 - induction heating

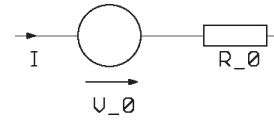
Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	°C
T_{stg}		-55...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
F_c	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case		30	pF
Weight			6	g

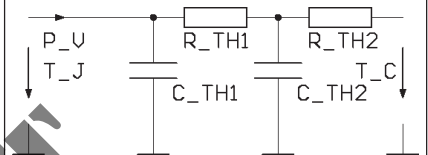
Equivalent Circuits for Simulation

Conduction



IGBT (typ. at $V_{GE} = 15 \text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 0.99 \text{ V}; R_0 = 25 \text{ m}\Omega$

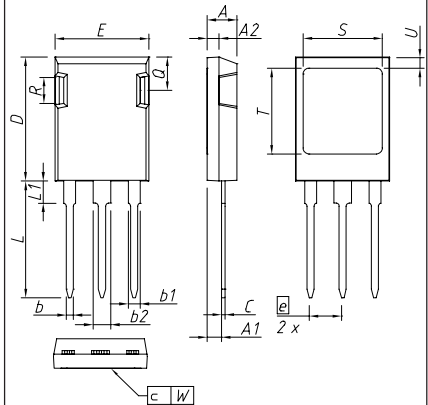
Thermal Response



IGBT (typ.)

$C_{th1} = 0.13 \text{ J/K}; R_{th1} = 0.06 \text{ K/W}$
 $C_{th2} = 0.32 \text{ J/K}; R_{th2} = 0.27 \text{ K/W}$

ISOPLUS247™ OUTLINE



DIM.	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,29	2,54	0,090	0,100
A2	1,91	2,16	0,075	0,085
b	1,14	1,40	0,045	0,055
b1	1,91	2,15	0,075	0,085
b2	2,92	3,20	0,115	0,126
C	0,61	0,83	0,024	0,033
D	20,80	21,34	0,819	0,840
E	15,75	16,13	0,620	0,635
e	5,45 BSC		0,215 BSC	
L	19,81	20,60	0,780	0,811
L1	3,81	4,38	0,150	0,172
Q	5,59	6,20	0,220	0,244
R	4,32	4,85	0,170	0,191
S	13,21	13,72	0,520	0,540
T	15,75	16,26	0,620	0,640
U	1,65	2,03	0,065	0,080
W	-	0,10	-	0,004

The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side
 This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except Lmax.

PHASE-OUT

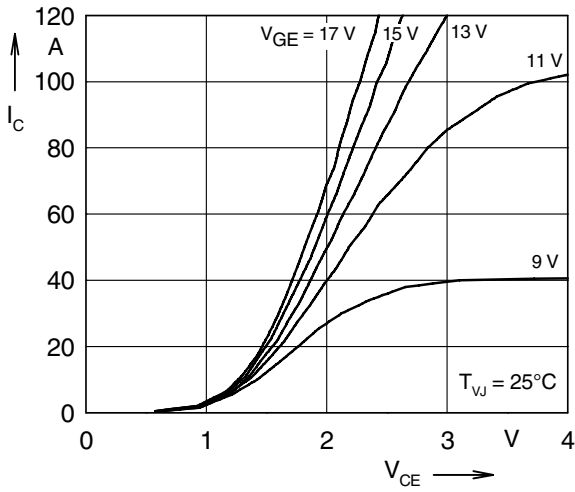


Fig. 1 Typ. output characteristics

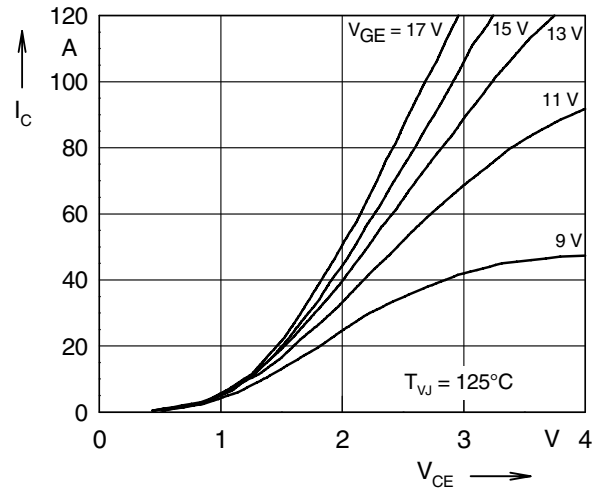


Fig. 2 Typ. output characteristics

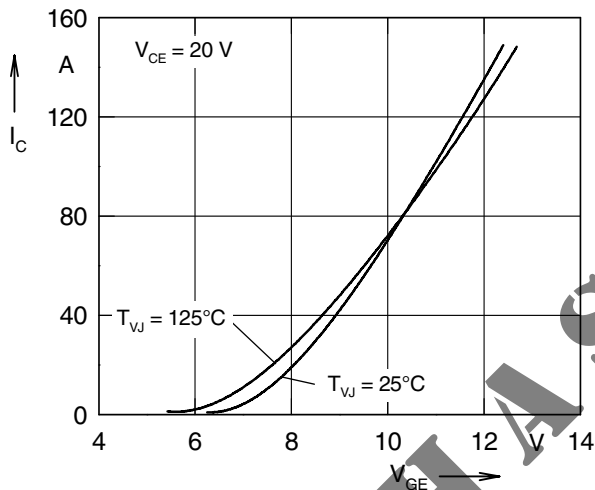


Fig. 3 Typ. transfer characteristics

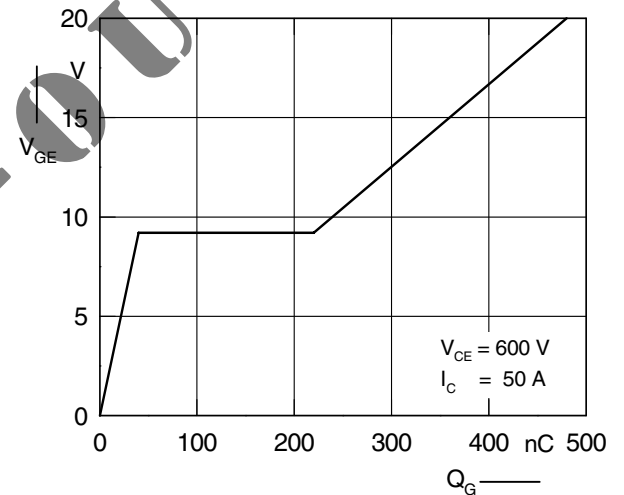


Fig. 4 Typ. turn on gate charge

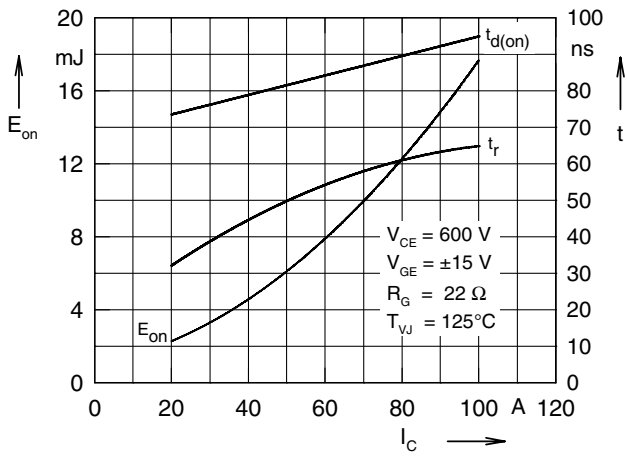


Fig. 5 Typ. turn on energy and switching times versus collector current

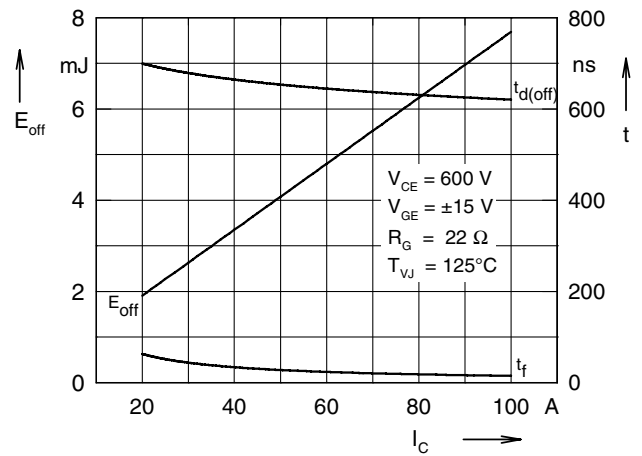


Fig. 6 Typ. turn off energy and switching times versus collector current

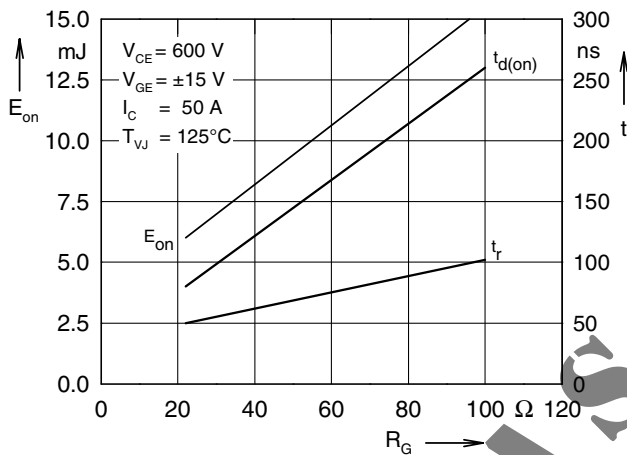


Fig. 7 Typ. turn on energy and switching times versus gate resistor

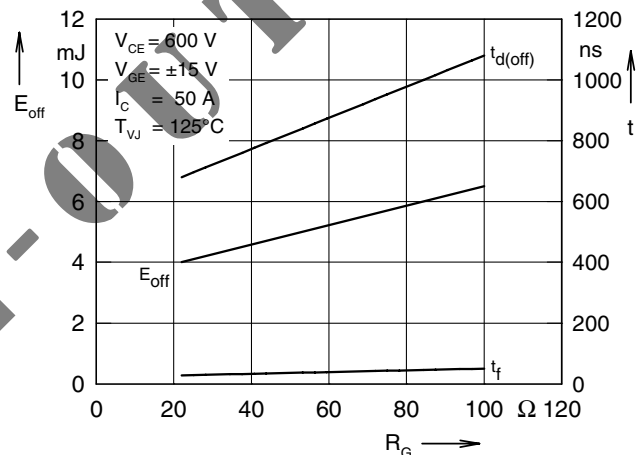


Fig. 8 Typ. turn off energy and switching times versus gate resistor

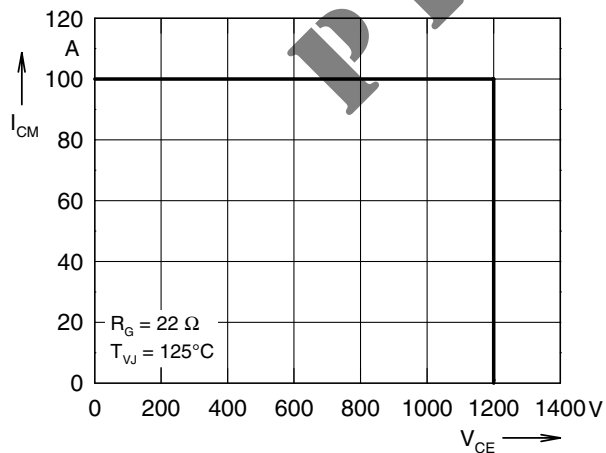


Fig. 9 Reverse biased safe operating area RBSOA

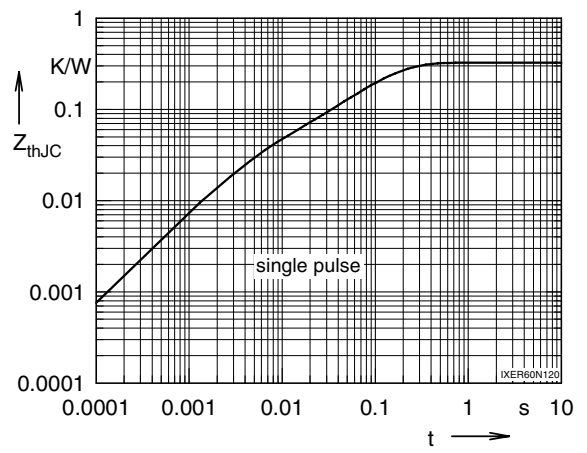


Fig. 10 Typ. transient thermal impedance